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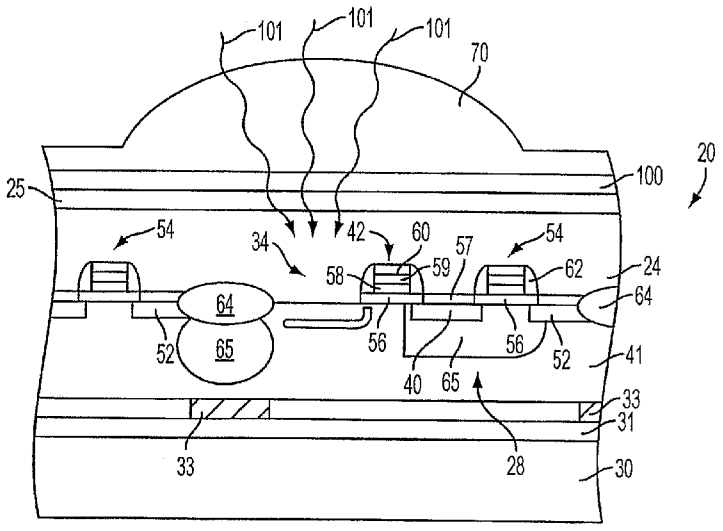
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(54) **Title:** BtFRIED DOPED REGION FOR VERTICAL ANTI-BLOOMING CONTROL AND CROSS-TALK REDUCTION FOR IMAGERS



(57) **Abstract:** The present invention provides a solid-state imager device (20) having a patterned buried doped region (33) in the substrate (30) , preferably an n+ doped region, that collects excess electrons and thus reduces cross-talk, minimizes blooming of excess electrons, and reduces dark current in a solid-state imager device, and a corresponding fabrication method.

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